MG150TF12E2A

VCES	1200V
IC	150A

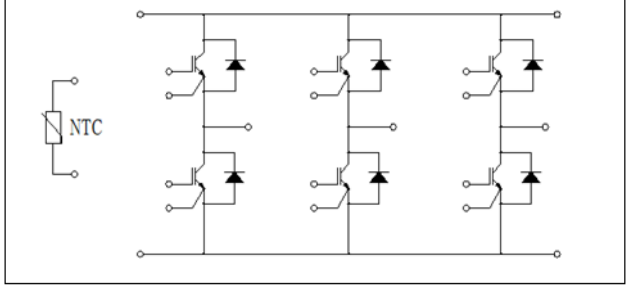
Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)

Features

- Low switching losses
- Low $V_{ce(sat)}$ with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Maximum junction temperature 175℃

Circuit



IGBT Modules

● IGBT- inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	V_{GE}=0V, I_C =1mA, T_{vj}=25℃	1200	V
Continuous Collector Current	I_C	T_c=100℃, T_{vjmax}=175℃	150	A
Repetitive Peak Collector Current	I_{CRM}	tp=1ms	300	A
Gate-Emitter Voltage	V_{GES}	T_{vj}=25℃	±20	V
Total Power Dissipation	P_{tot}	T_c=25℃ T_{vjmax}=175℃	715	W

IGBT

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, I_C =4mA,T_{vj}=25℃	5.0	5.8	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	V_{CE}=1200V,V_{GE}=0V,T_{vj}=25℃			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	Ic=150A,V_{GE}=15V, T_{vj}=25℃		1.90	2.25	V
		Ic=150A,V_{GE}=15V, T_{vj}=125℃		2.15		
Gate Charge	Q_G			1.42		uC
Input Capacitance	C_{ies}	V_{CE}=25V,V_{GE} =0V, f=1MHz,T_{vj}=25℃		9.82		nF
Reverse Transfer Capacitance	C_{res}			0.49		nF
Internal Gate Resistance	R_{gint}			5.0		Ω
Gate-Emitter leakage current	I_{GES}	V_{CE}=0 V, V_{GE}=20V,T_{vj} = 25℃			400	nA
Turn-on Delay Time	$t_{d(on)}$	I_C =150 A V_{CE} = 600 V V_{GE} = ±15V R_G =3.3Ω T_{vj}=25℃		112		ns
Rise Time	t_r			65		ns
Turn-off Delay Time	$t_{d(off)}$			257		ns
Fall Time	t_f			211		ns
Energy Dissipation During Turn-on Time	E_{on}			10.75		mJ
Energy Dissipation During Turn-off Time	E_{off}			11.50		mJ
Turn-on Delay Time	$t_{d(on)}$	I_C =150 A V_{CE} = 600 V V_{GE} = ±15V R_G =3.3Ω T_{vj}=125℃		156		ns
Rise Time	t_r			85		ns
Turn-off Delay Time	$t_{d(off)}$			304		ns
Fall Time	t_f			278		ns
Energy Dissipation During Turn-on Time	E_{on}			15.5		mJ
Energy Dissipation During Turn-off Time	E_{off}			17.3		mJ
SC Data	I_{sc}	T_p≤10us,V_{GE}=15V,T_{vj}=150℃, V_{cc}=900V,V_{CEM}≤1200V		675		A

Diode

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	T_{vj}=25℃	1200	V
Continuous DC Forward Current	I_F		150	A
Repetitive Peak Forward Current	I_{FRM}	t_p=1ms	300	A
I^2t-value	I^2t	V_R=0,t_p=10ms,T_{vj}=125℃	4550	A^2s

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	I_F=150A,T_{vj}=25℃		2.15		V
		I_F=150A,T_{vj}=125℃		1.95		
Recovered Charge	Q_{rr}	I_F =150 A V_R=600V -di_F/dt =900A/us T_{vj}=25℃		8.52		uC
Peak Reverse Recovery Current	I_{rr}			62		A
Reverse Recovery Energy	E_{rec}			7.25		mJ
Recovered Charge	Q_{rr}	I_F =150 A V_R=600V -di_F/dt =900A/us T_{vj}=125℃		17.6		uC
Peak Reverse Recovery Current	I_{rr}			97		A
Reverse Recovery Energy	E_{rec}			13.5		mJ

NTC-Thermistor

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		kΩ
Deviation of R100	ΔR/R	T_C=100,R_{100}=493.3Ω	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	R_2=R_{25}exp[$B_{25/50}$(1/T_2-1/(298.15 K))]		3375		K

Module Characteristics

T_C=25°C unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V_{isol}	t=1min,f=50Hz	2500			V
Maximum Junction Temperature	T_{jmax}				175	℃
Operating Junction Temperature	$T_{vj\ op}$		-40		150	℃
Storage Temperature	T_{stg}		-40		125	℃
Stray-inductance-module	L_{SCE}			21		nH
Module lead resistance, terminals-chip	$R_{cc'+EE'}$	T_C=25℃, per switch		1.9		mΩ
	$R_{AA'+CC'}$			1.5		
Thermal Resistance Junction-to Case	$R_{\theta JC}$	per IGBT-inverter			0.21	K/W
		per Diode-inverter			0.32	
Thermal Resistance Case-to Sink	$R_{\theta CS}$	per IGBT-inverter		0.09		K/W
		per Diode-inverter		0.15		
Mounting Force Per Clamp	F		3.0		6.0	N
Weight of Module	G			300		g

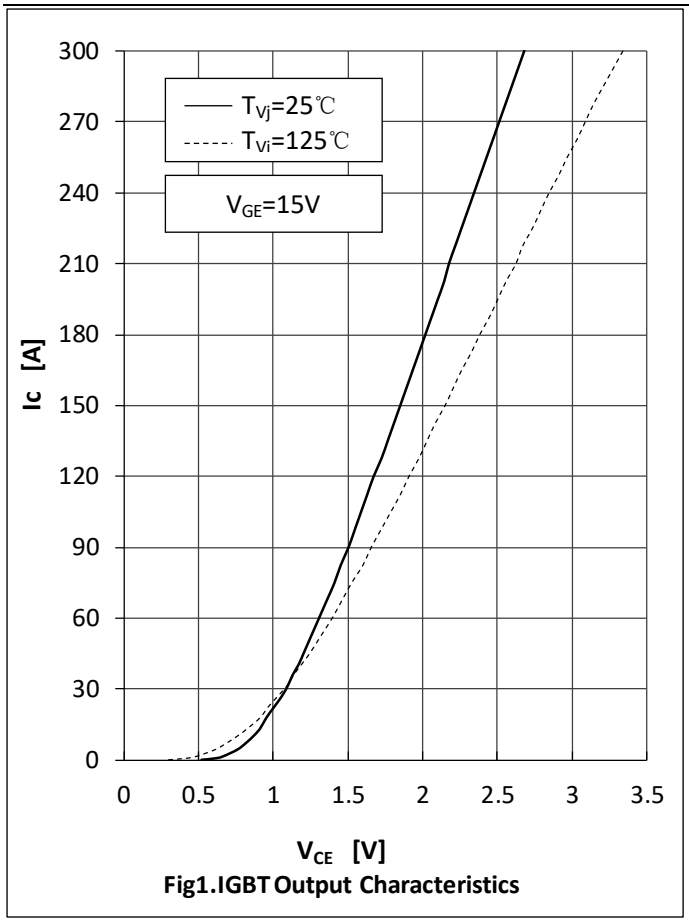


Fig1.IGBT Output Characteristics

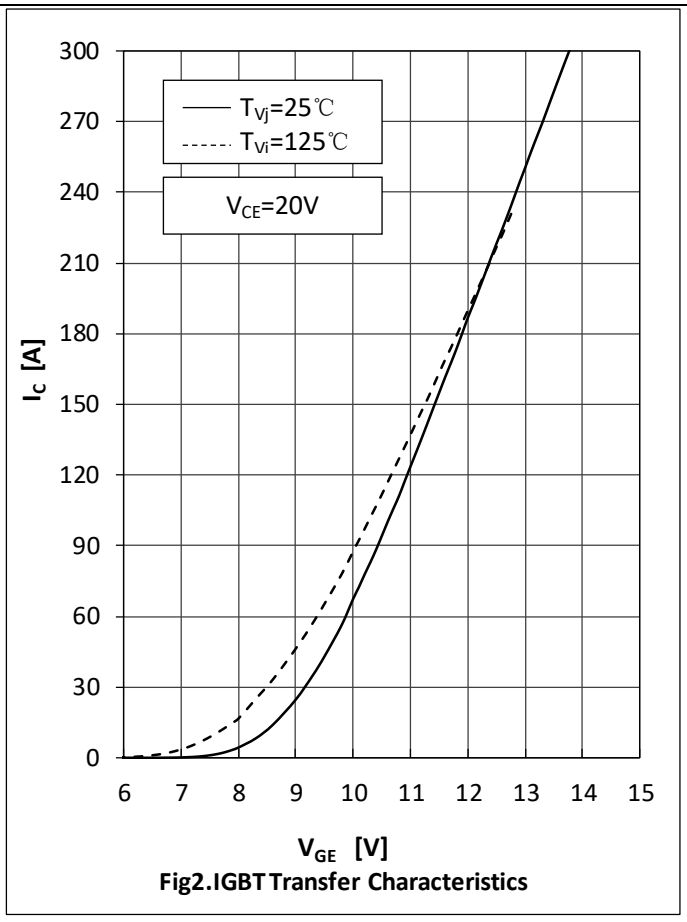


Fig2.IGBT Transfer Characteristics

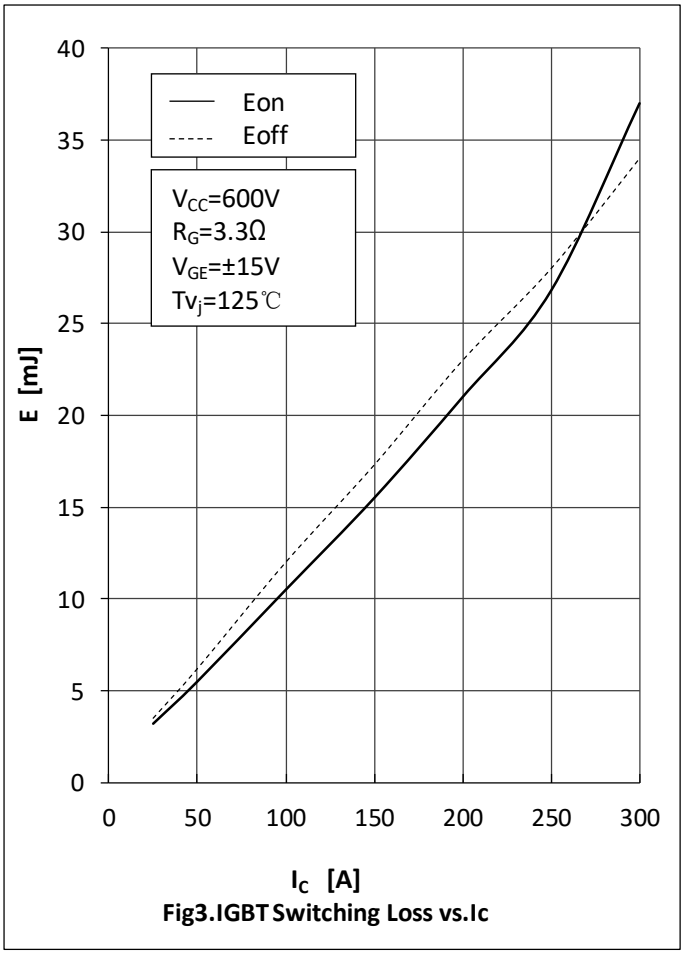


Fig3.IGBT Switching Loss vs.Ic

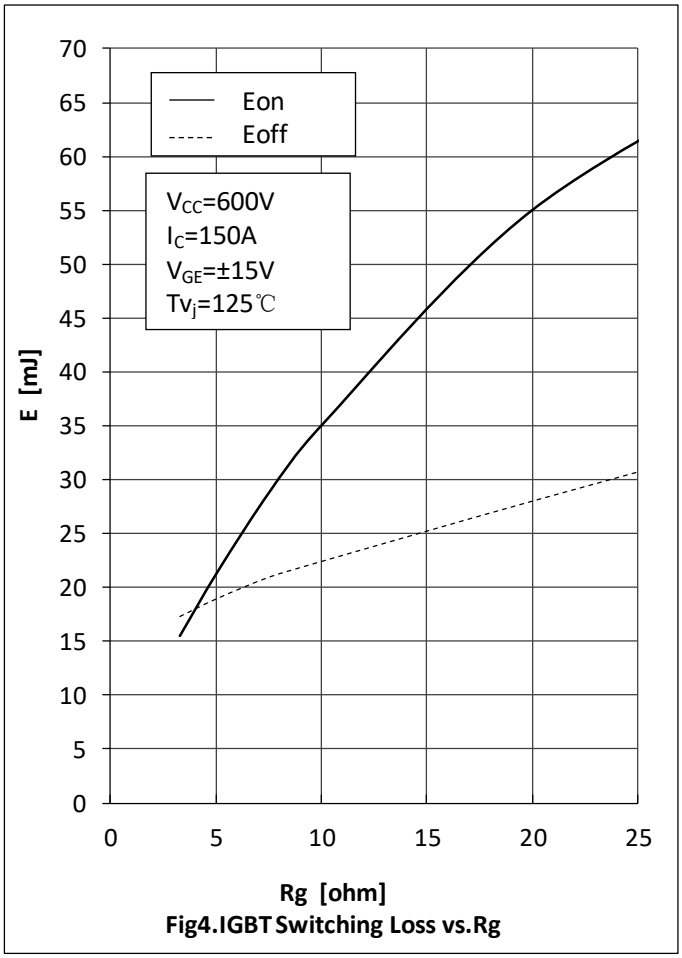


Fig4.IGBT Switching Loss vs.Rg

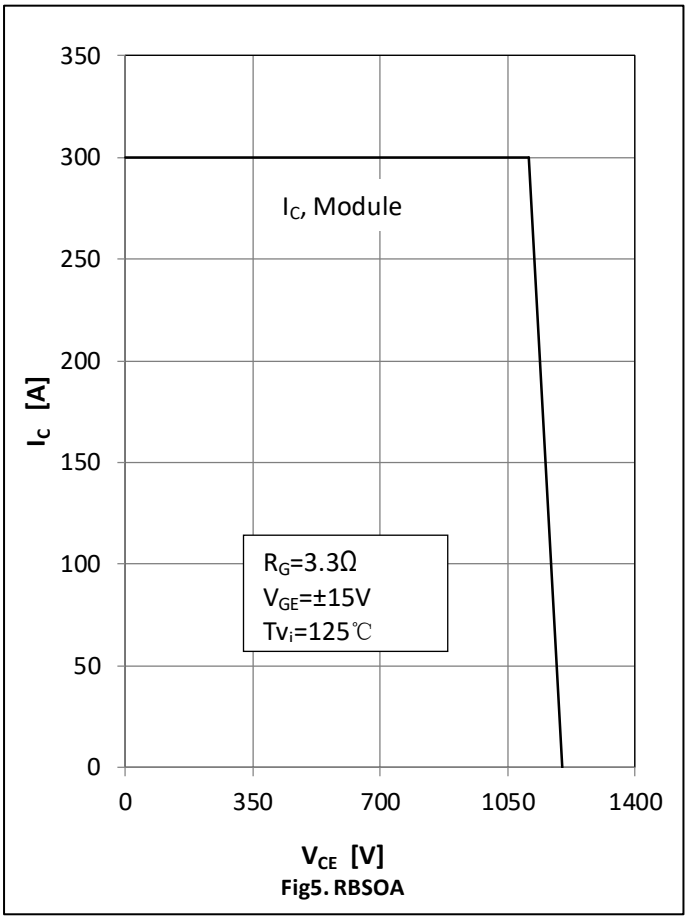


Fig5. RBSOA

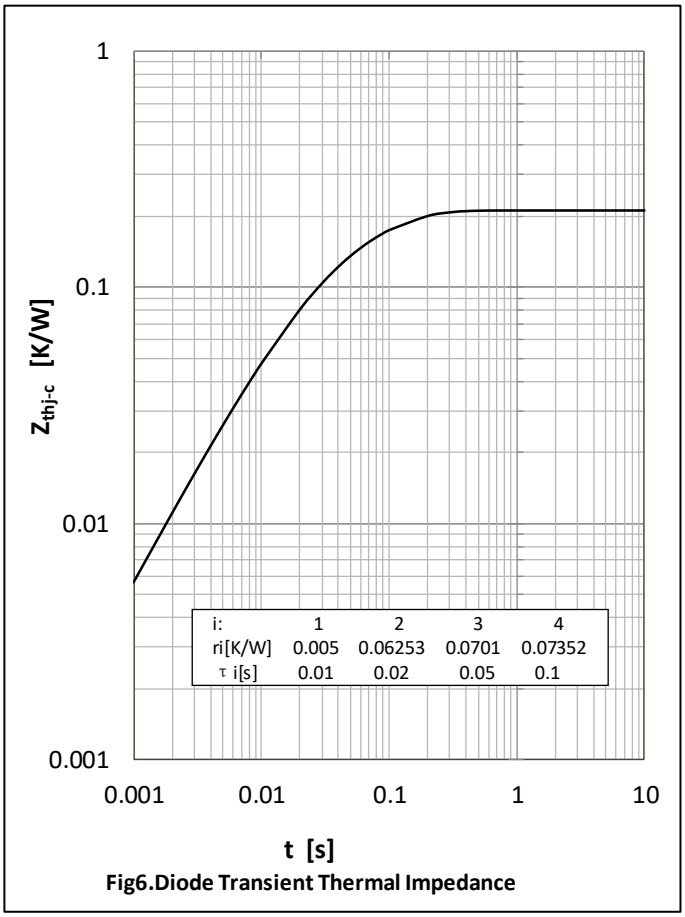


Fig6.Diode Transient Thermal Impedance

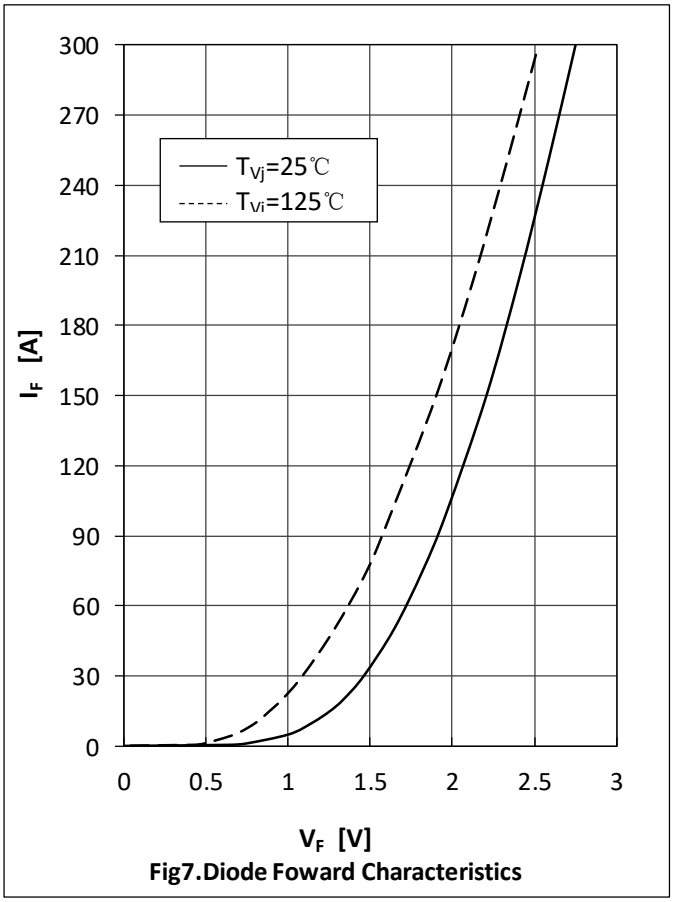


Fig7.Diode Foward Characteristics

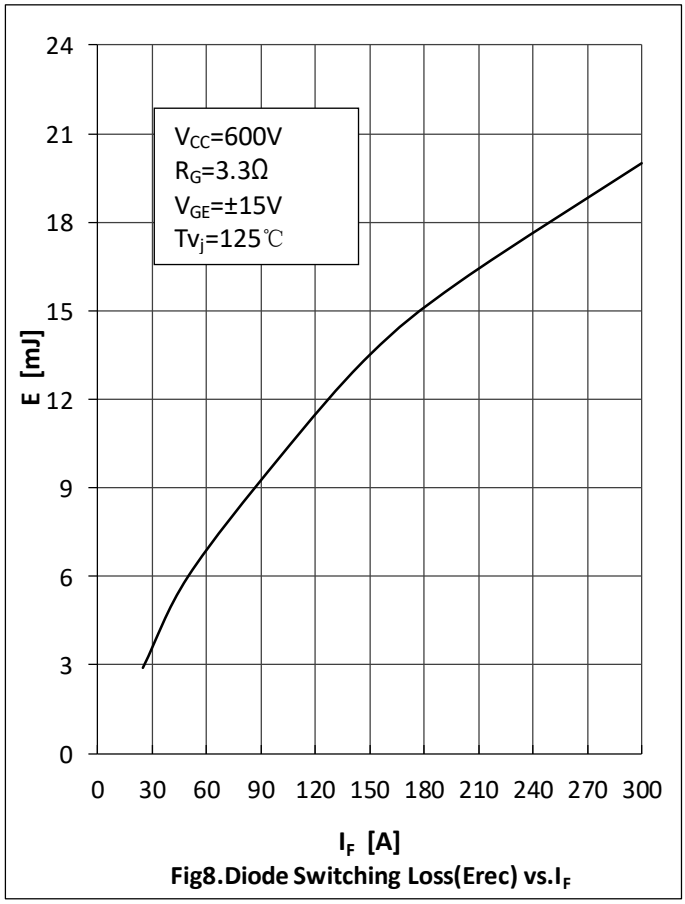


Fig8.Diode Switching Loss(Erec) vs.I_F

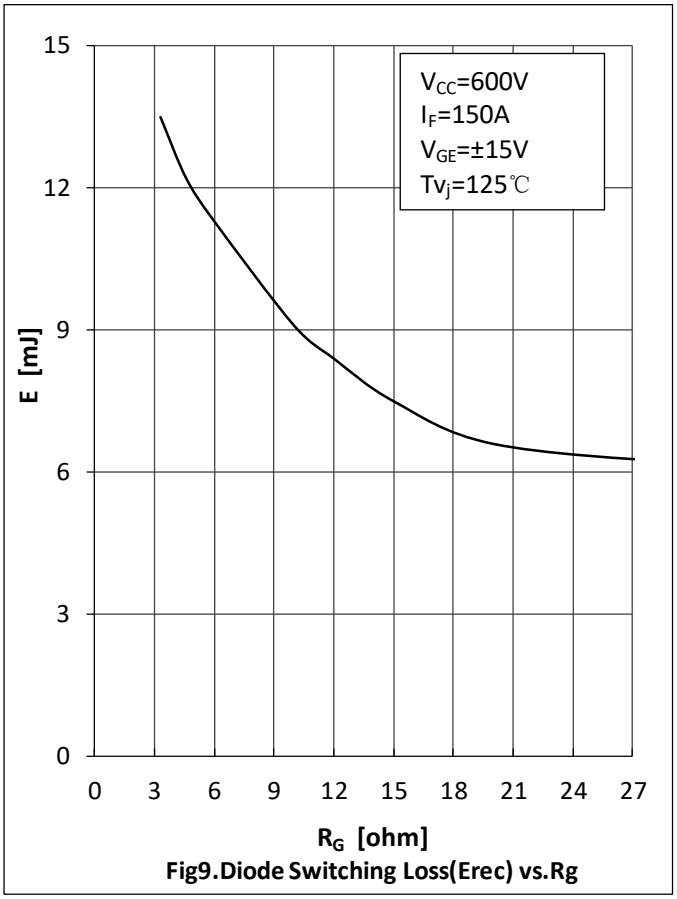


Fig9.Diode Switching Loss(Erec) vs.Rg

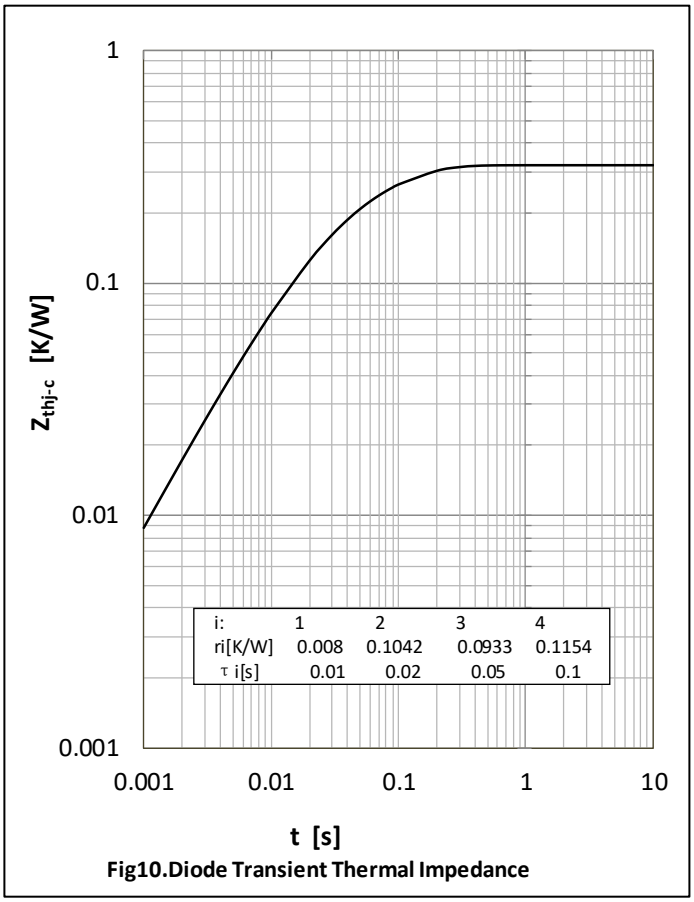


Fig10.Diode Transient Thermal Impedance

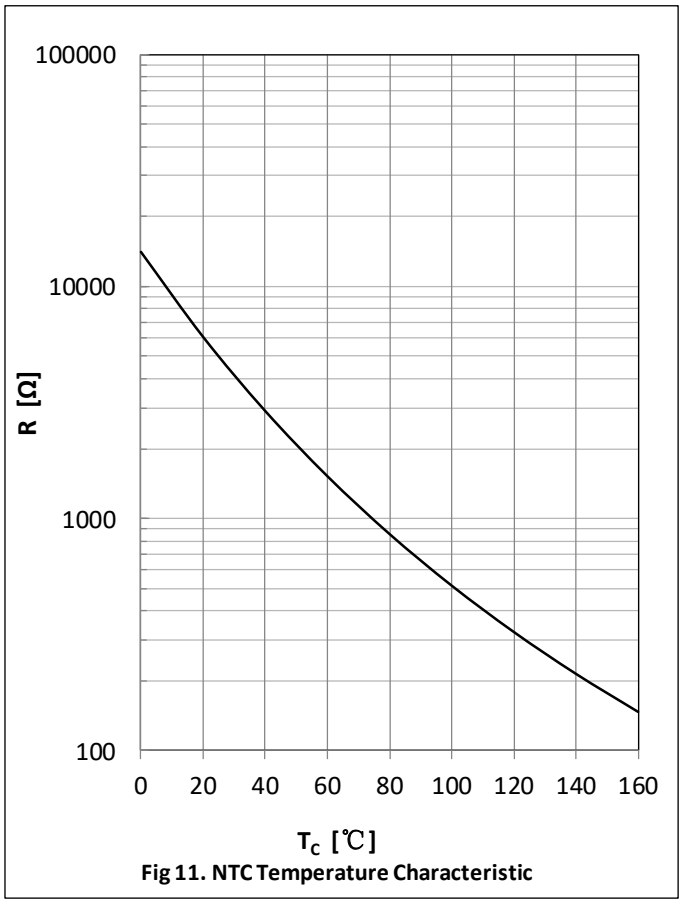
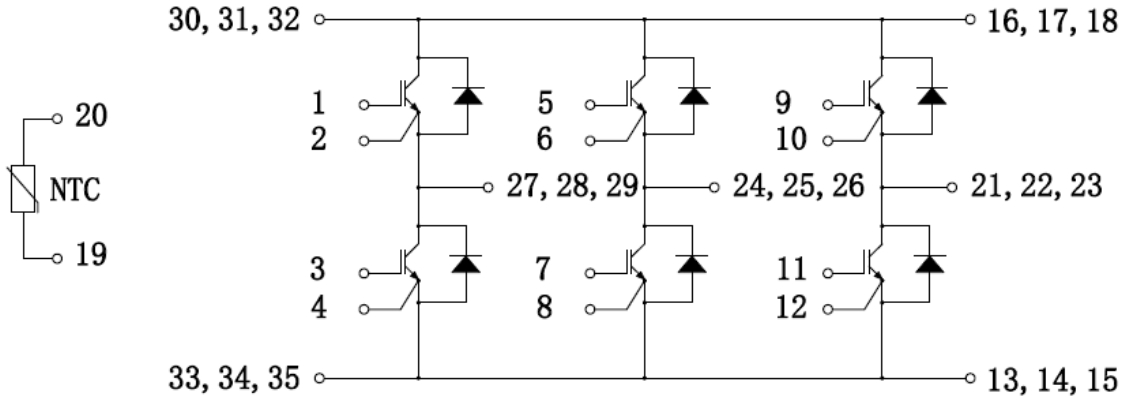
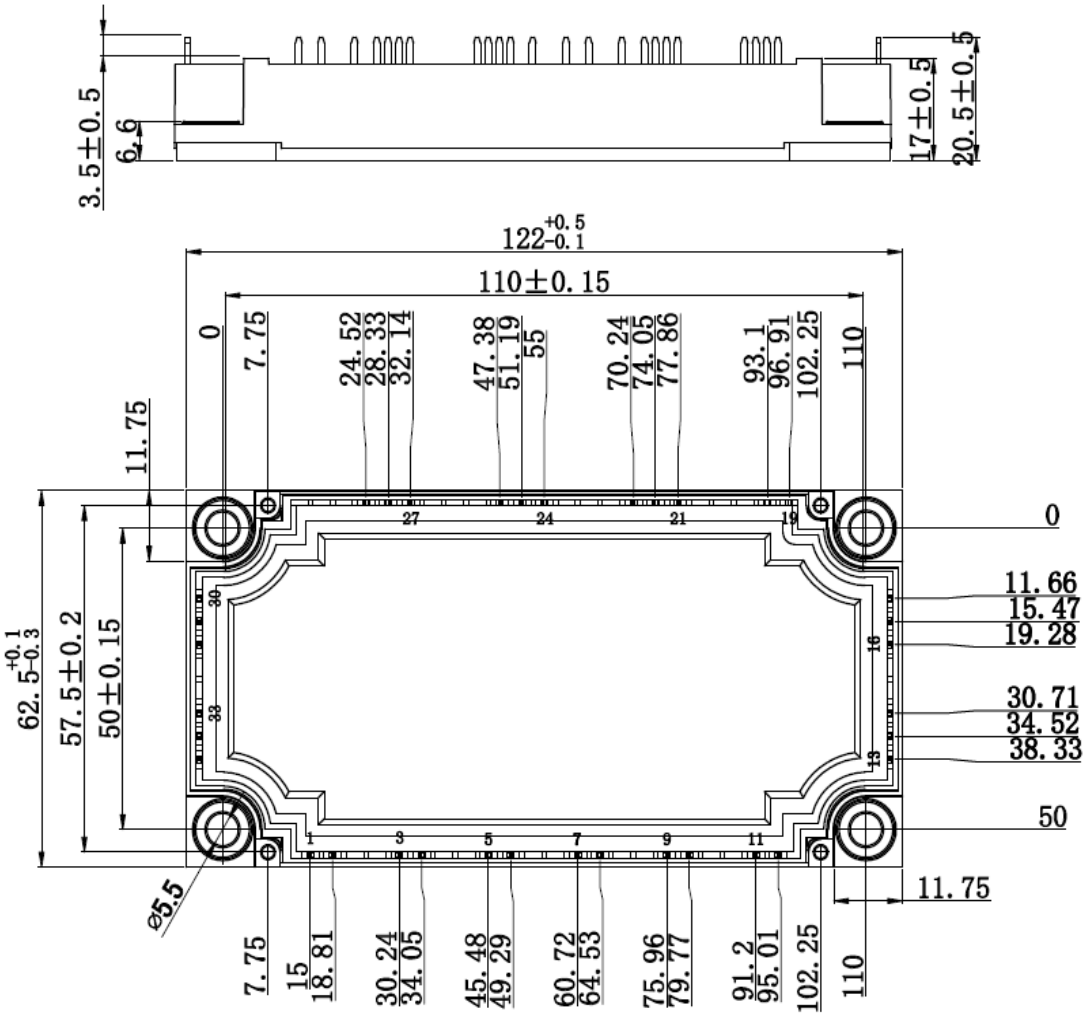


Fig 11. NTC Temperature Characteristic

- **Circuit Diagram**



- **Package Outline Information**



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